

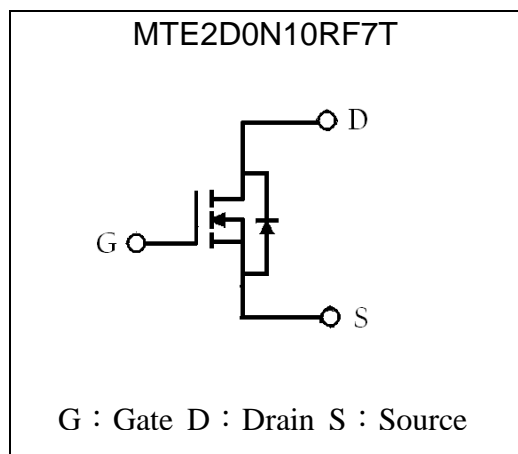
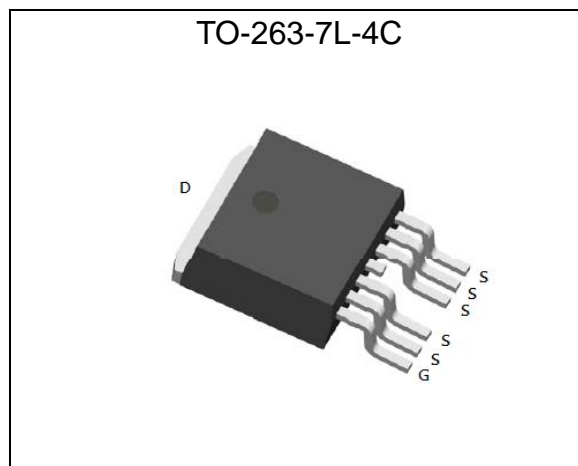
N-Channel Enhancement Mode Power MOSFET

MTE2D0N10RF7T

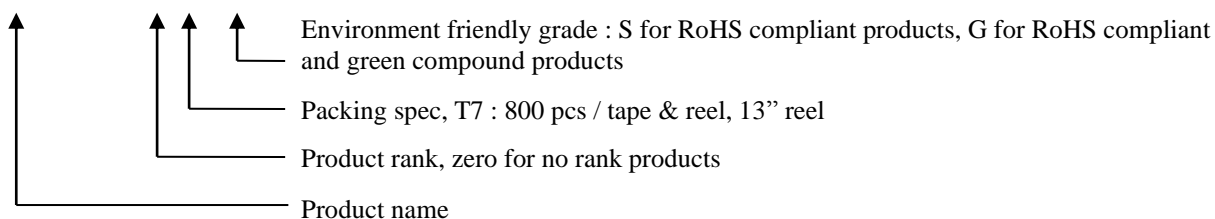
Features

- Low On Resistance
- Low Gate Charge
- Fast Switching Characteristic
- RoHS compliant package

| | |
|---|---------------|
| BV_{DSS} | 100V |
| I_D @ $V_{GS}=10V$, $T_C=25^\circ C$ (silicon limit) | 215A |
| I_D @ $V_{GS}=10V$, $T_C=25^\circ C$ (package limit) | 170A |
| I_D @ $V_{GS}=10V$, $T_A=25^\circ C$ | 33A |
| $R_{DSON(TYP)}$ @ $V_{GS}=10V$, $I_D=50A$ | 2.2m Ω |

Symbol

Outline

Ordering Information

| Device | Package | Shipping |
|----------------------|---|-----------------------|
| MTE2D0N10RF7T-0-T7-X | TO-263-7L-4C (Pb-free lead plating and RoHS compliant package) | 800 pcs / Tape & Reel |



**Absolute Maximum Ratings** ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

| Parameter | Symbol | Limits | Unit | |
|--|----------------|------------------------------------|--------------------|-----|
| Drain-Source Voltage | V_{DS} | 100 | V | |
| Gate-Source Voltage | V_{GS} | ± 20 | | |
| Continuous Drain Current @ $T_C=25^{\circ}\text{C}$ (silicon limit) | I_D | 215 | A | |
| Continuous Drain Current @ $T_C=100^{\circ}\text{C}$ (silicon limit) | | 150 | | |
| Continuous Drain Current @ $T_C=25^{\circ}\text{C}$ (package limit) (Note 1) | | 170 | | |
| Continuous Drain Current @ $T_A=25^{\circ}\text{C}$ (Note 2) | | 33 | | |
| Continuous Drain Current @ $T_A=70^{\circ}\text{C}$ (Note 2) | | 28 | | |
| Pulsed Drain Current (Note 3) | | I_{DM} | | 680 |
| Avalanche Current @ $L=0.1\text{mH}$ (Note 3) | I_{AS} | 30 | | |
| Avalanche Energy @ $L=0.5\text{mH}$ | E_{AS} | 72 | mJ | |
| Power Dissipation | P_D | $T_C=25^{\circ}\text{C}$ (Note 1) | 227 | W |
| | | $T_C=100^{\circ}\text{C}$ (Note 1) | 113 | |
| Power Dissipation | P_{DSM} | $T_A=25^{\circ}\text{C}$ (Note 2) | 5.4 | |
| | | $T_A=70^{\circ}\text{C}$ (Note 2) | 3.8 | |
| Operating Junction and Storage Temperature | T_j, T_{stg} | $-55\sim+175$ | $^{\circ}\text{C}$ | |

Thermal Data

| Parameter | Symbol | Value | Unit |
|--|-----------------|-------|-----------------------------|
| Thermal Resistance, Junction-to-case, max | $R_{\theta JC}$ | 0.66 | $^{\circ}\text{C}/\text{W}$ |
| Thermal Resistance, Junction-to-ambient, max, (Note 2) | $R_{\theta JA}$ | 27.6 | |

- Note : 1. The power dissipation P_D is based on $T_{J(MAX)}=175^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.
3. Pulse width limited by junction temperature $T_{J(MAX)}=175^{\circ}\text{C}$. Ratings are based on low frequency and low duty cycles to keep initial $T_J=25^{\circ}\text{C}$.
4. The static characteristics are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% maximum.
5. The $R_{\theta JA}$ is the sum of thermal resistance from junction to case $R_{\theta JC}$ and case to ambient.



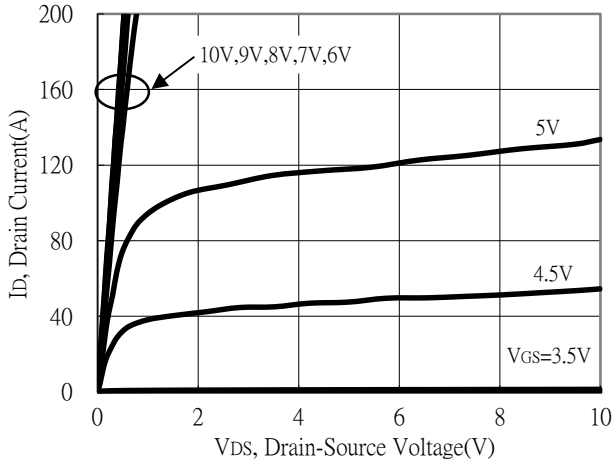
Characteristics (Tc=25°C, unless otherwise specified)

| Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|---------------------------|------|------|------|------|---|
| Static | | | | | |
| BV _{DSS} | 100 | - | - | V | V _{GS} =0V, I _D =250μA |
| V _{GS(th)} | 2 | - | 4 | | V _{DS} = V _{GS} , I _D =250μA |
| G _{FS} | - | 52.3 | - | S | V _{DS} =5V, I _D =20A |
| I _{GSS} | - | - | ±100 | nA | V _{GS} =±20V, V _{DS} =0V |
| I _{DSS} | - | - | 1 | μA | V _{DS} =80V, V _{GS} =0V |
| | - | - | 10 | | V _{DS} =80V, V _{GS} =0V, T _J =85°C |
| *R _{DS(ON)} | - | 2.2 | 2.8 | mΩ | V _{GS} =10V, I _D =30A |
| Dynamic | | | | | |
| *Q _g | - | 125 | - | nC | V _{DS} =50V, I _D =30A, V _{GS} =10V |
| *Q _{gs} | - | 35 | - | | |
| *Q _{gd} | - | 30 | - | | |
| *t _{d(ON)} | - | 45 | - | ns | V _{DS} =50V, I _D =30A, V _{GS} =10V, R _G =1Ω |
| *t _r | - | 30 | - | | |
| *t _{d(OFF)} | - | 88 | - | | |
| *t _f | - | 27 | - | | |
| C _{iss} | - | 8100 | - | pF | V _{DS} =50V, V _{GS} =0V, f=1MHz |
| C _{oss} | - | 1230 | - | | |
| C _{rss} | - | 45 | - | | |
| R _g | - | 1.0 | - | Ω | f=1MHz |
| Source-Drain Diode | | | | | |
| *I _S | - | - | 30 | A | |
| *I _{SM} | - | - | 120 | | |
| *V _{SD} | - | 0.8 | 1.2 | V | I _S =30A, V _{GS} =0V |
| *t _{rr} | - | 75 | - | ns | I _F =30A, V _{GS} =0V, dI _F /dt=100A/μs |
| *Q _{rr} | - | 150 | - | nC | |

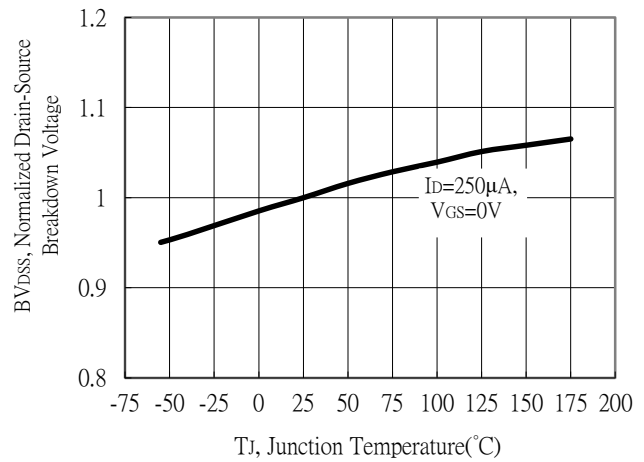
*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

Typical Characteristics

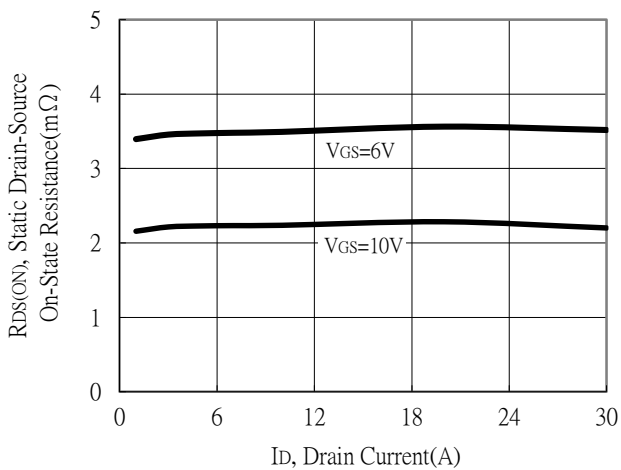
Typical Output Characteristics



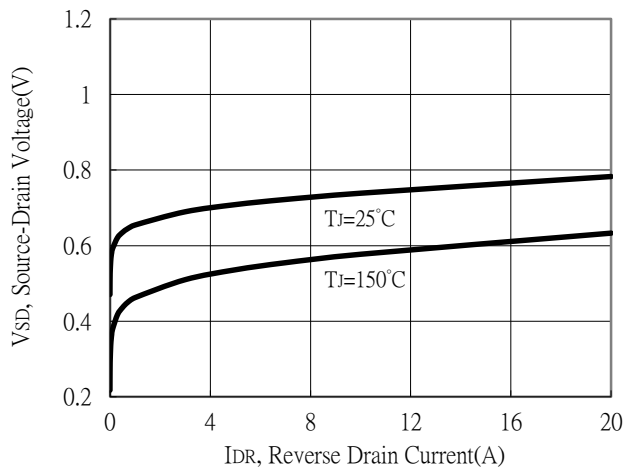
Brekdown Voltage vs Ambient Temperature



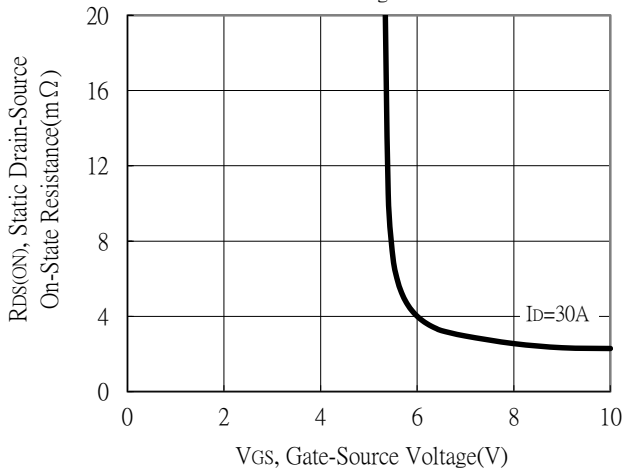
Static Drain-Source On-State resistance vs Drain Current



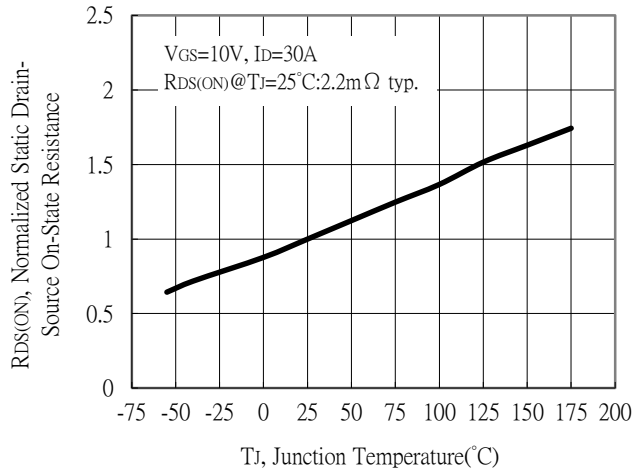
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

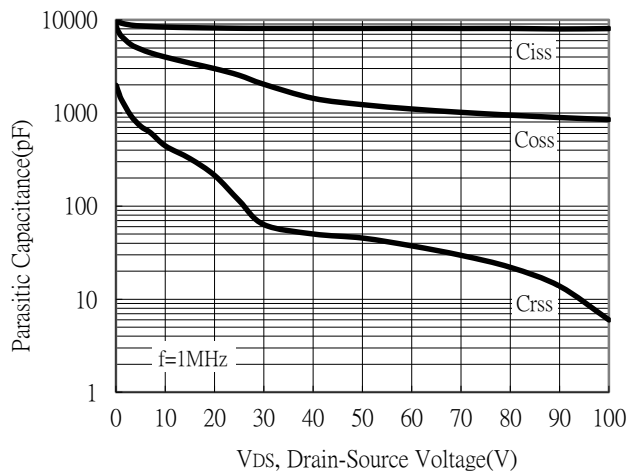


Drain-Source On-State Resistance vs Junction Temperature

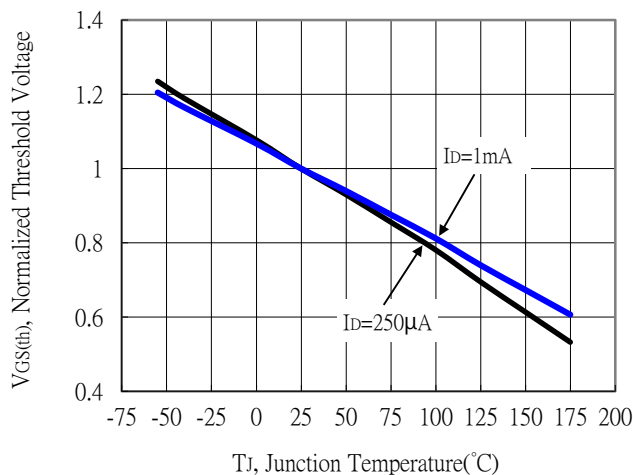


Typical Characteristics(Cont.)

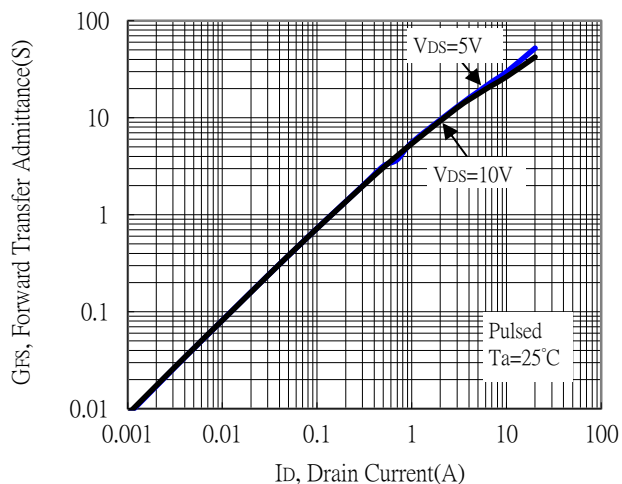
Capacitance vs Drain-to-Source Voltage



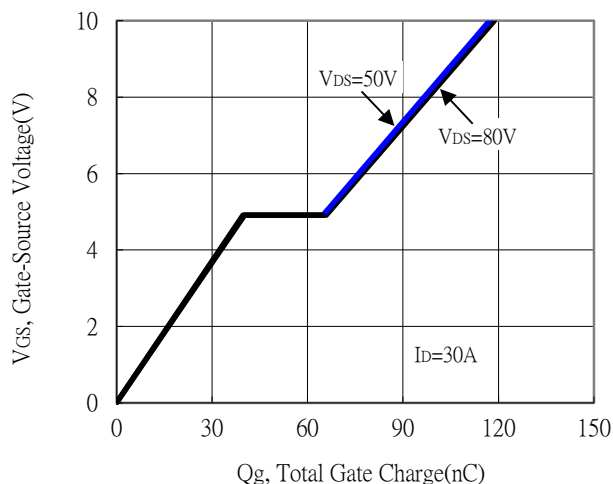
Threshold Voltage vs Junction Temperature



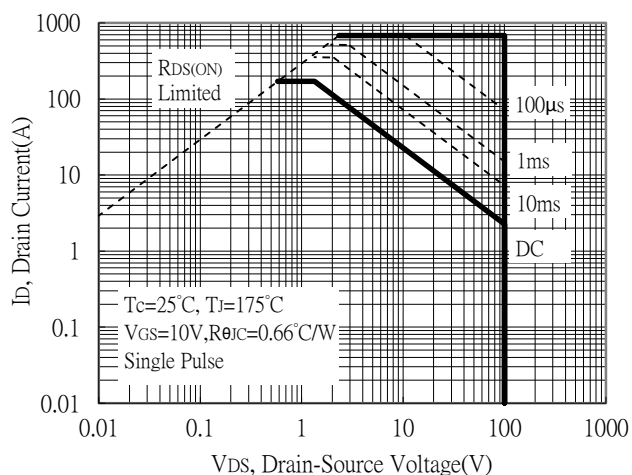
Forward Transfer Admittance vs Drain Current



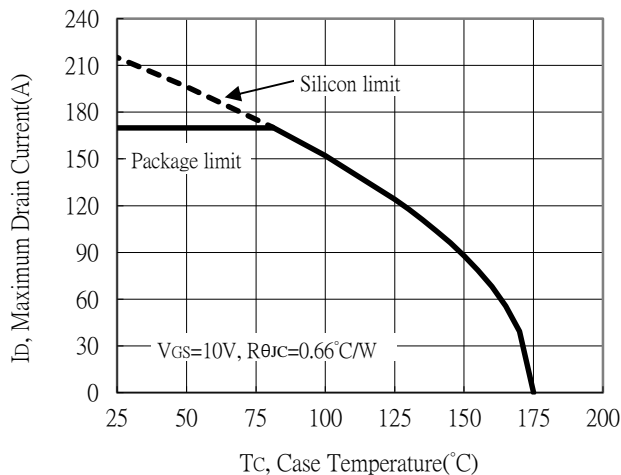
Gate Charge Characteristics



Maximum Safe Operating Area

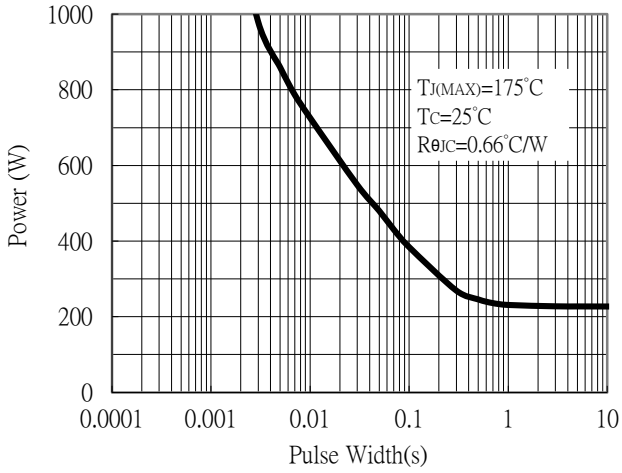


Maximum Drain Current vs Case Temperature

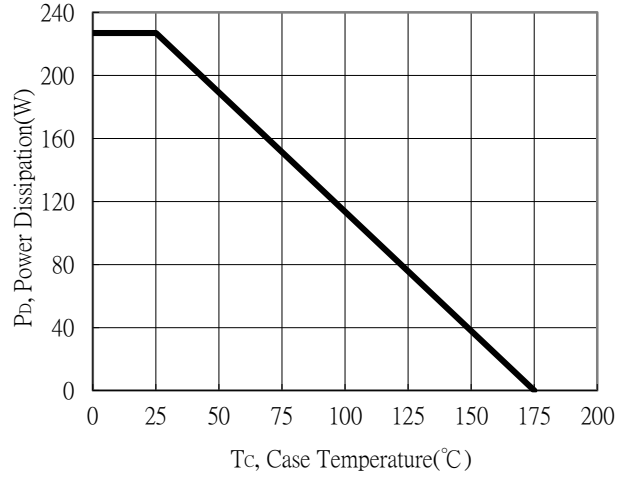


Typical Characteristics(Cont.)

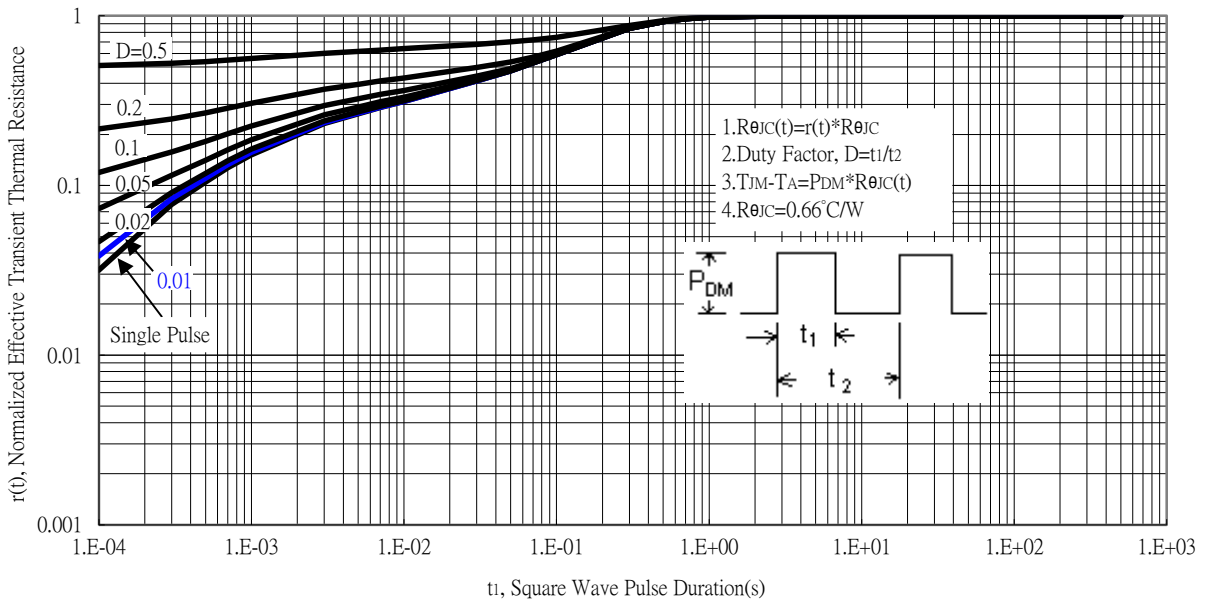
Single Pulse Maximum Power Dissipation



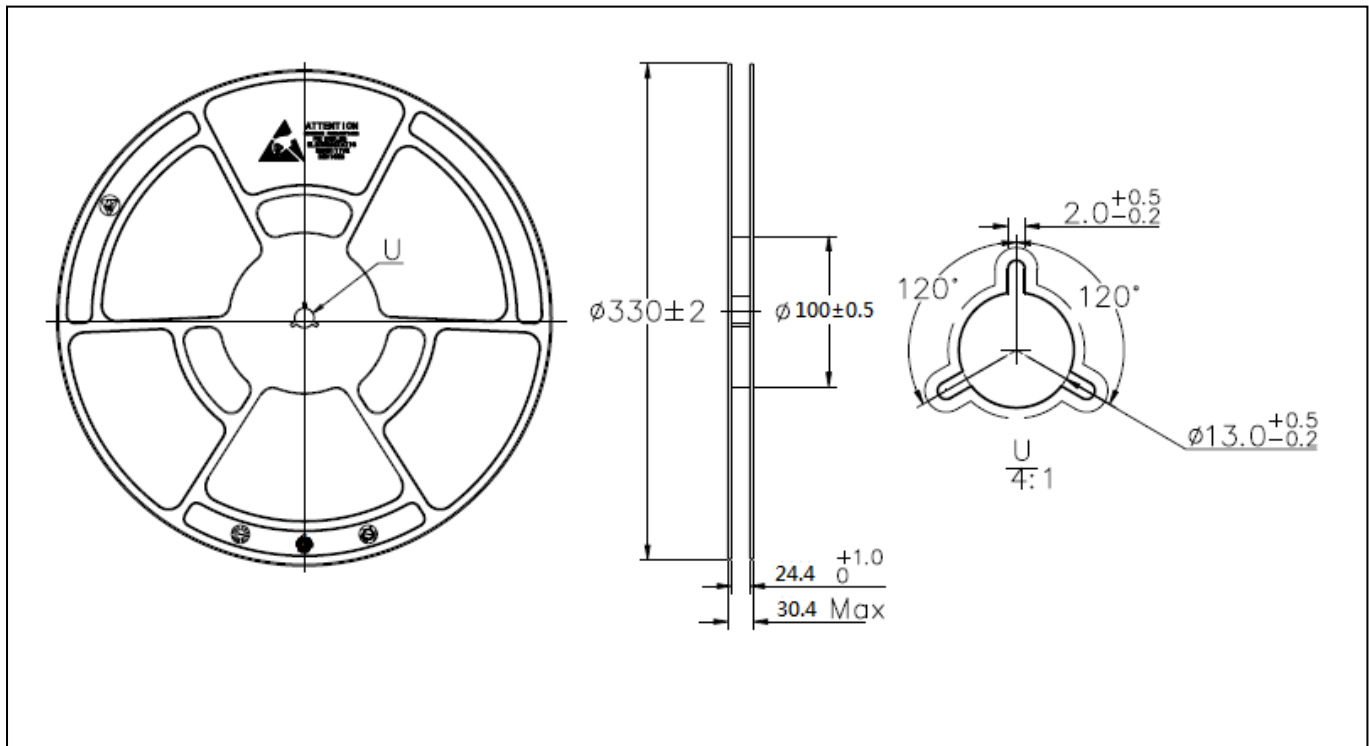
Power Derating Curve



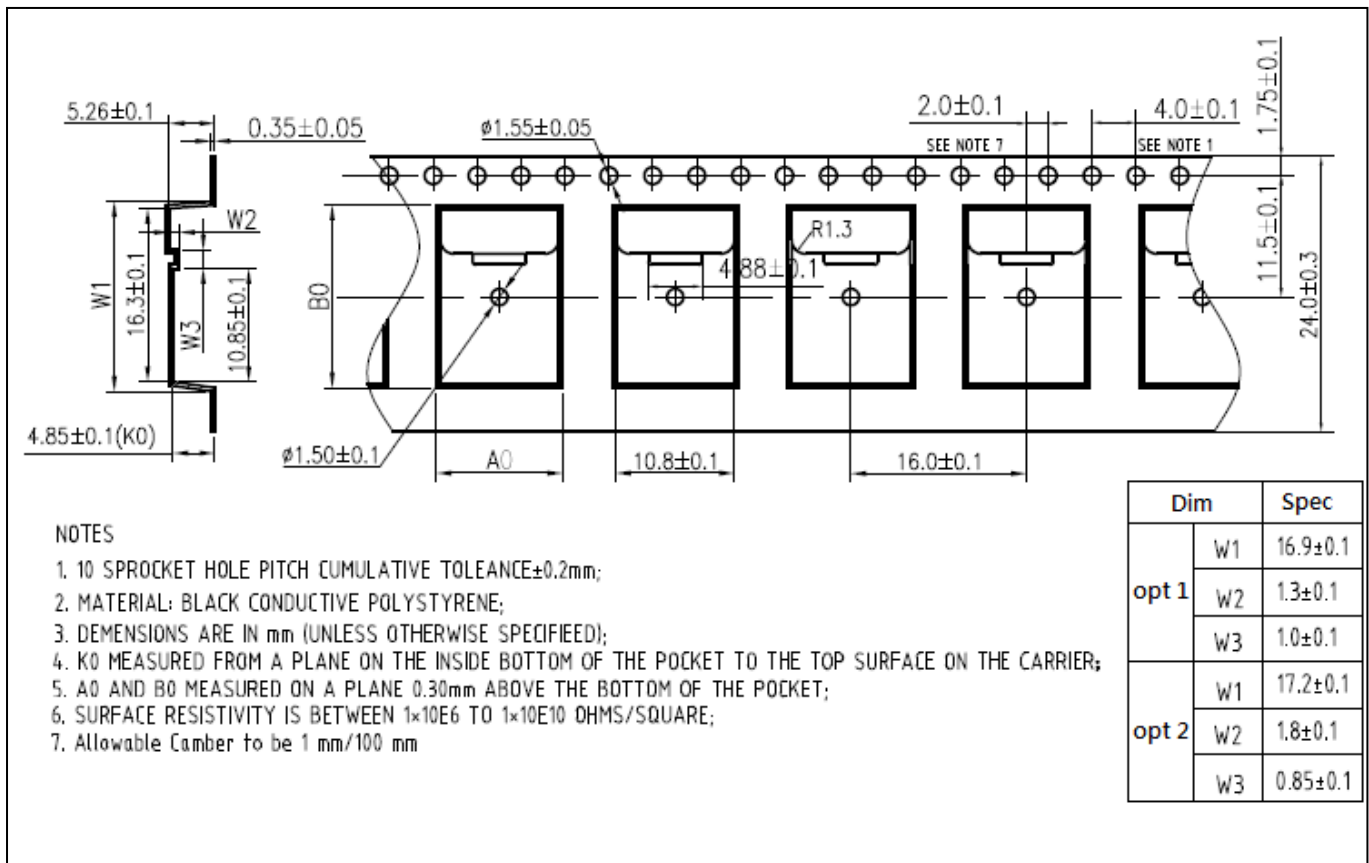
Transient Thermal Response Curves



Reel Dimension



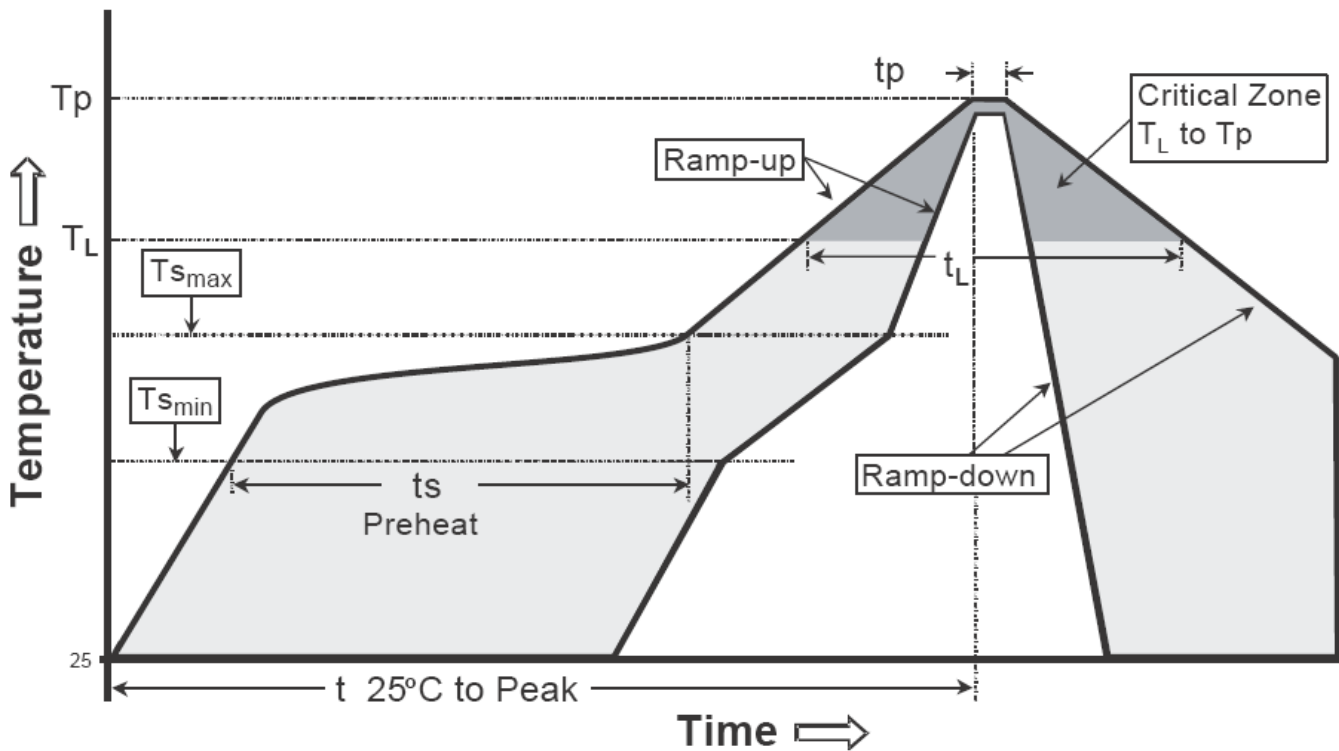
Carrier Tape Dimension



Recommended wave soldering condition

| | | |
|-----------------|------------------|-----------------|
| Product | Peak Temperature | Soldering Time |
| Pb-free devices | 260 +0/-5 °C | 5 +1/-1 seconds |

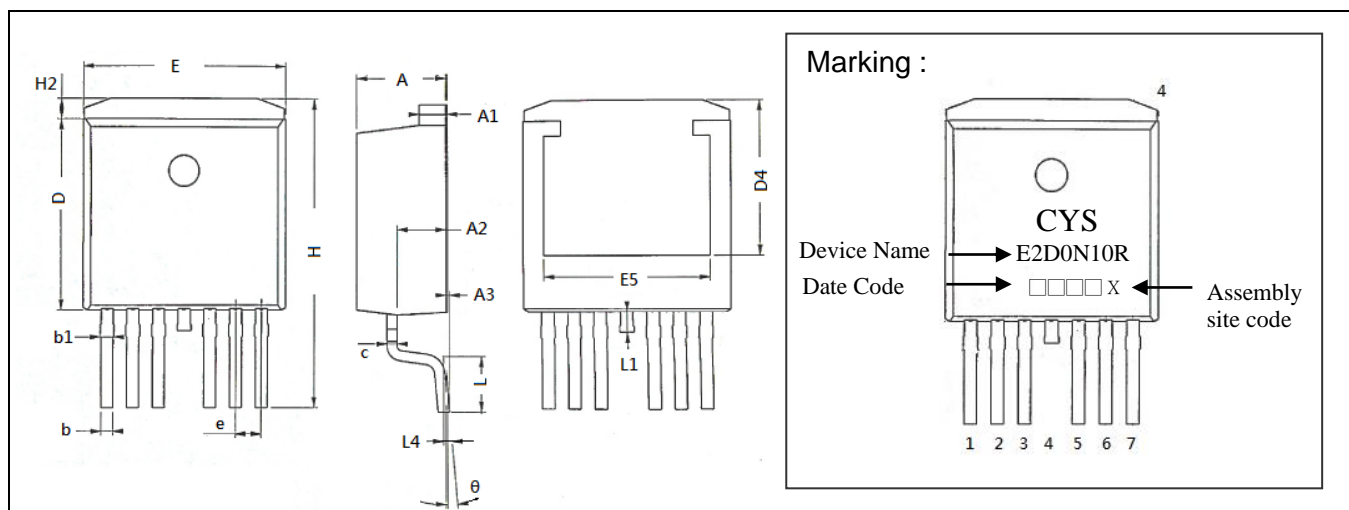
Recommended temperature profile for IR reflow



| Profile feature | Sn-Pb eutectic Assembly | Pb-free Assembly |
|--|-------------------------|------------------|
| Average ramp-up rate (Tsmax to Tp) | 3°C/second max. | 3°C/second max. |
| Preheat | | |
| -Temperature Min(Ts min) | 100°C | 150°C |
| -Temperature Max(Ts max) | 150°C | 200°C |
| -Time(ts min to ts max) | 60-120 seconds | 60-180 seconds |
| Time maintained above: | | |
| -Temperature (Tl) | 183°C | 217°C |
| - Time (tl) | 60-150 seconds | 60-150 seconds |
| Peak Temperature(Tp) | 240 +0/-5 °C | 260 +0/-5 °C |
| Time within 5°C of actual peak temperature(tp) | 10-30 seconds | 20-40 seconds |
| Ramp down rate | 6°C/second max. | 6°C/second max. |
| Time 25 °C to peak temperature | 6 minutes max. | 8 minutes max. |

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-263-7L-4C Dimension



Marking :

Device Name → E2D0N10R
 Date Code → □□□X ← Assembly site code

Style : Pin 1. Gate
 Pin 2, 3, 5, 6, 7 : Source
 Pin 4. Drain

7-Lead Plastic Surface Mounted TO-263-7L Package
 CYStek Package Code : F7T

Date Code : (From left to right)
 First Code : Year code, the last digit of Christnr year. For example, 2014→4, 2015→, 2016→6, ..., etc.
 Second Code : Month code, Jan→A, Feb→B, Mar→C, Apr→D, May→E, Jun→F, Jul→G, Aug→H, Sep→J, Oct→K, Nov→L, Dec→M
 Third and fourth codes : production serial number, 01~99

*:Typical

| DIM | Inches | | Millimeters | | DIM | Inches | | Millimeters | |
|-----|--------|--------|-------------|------|-----|--------|--------|-------------|-------|
| | Min. | Max. | Min. | Max. | | Min. | Max. | Min. | Max. |
| A | 0.1673 | 0.1791 | 4.25 | 4.55 | E | 0.3858 | 0.4016 | 9.80 | 10.20 |
| A1 | 0.0472 | 0.0551 | 1.20 | 1.40 | e | 0.0500 | BSC | 1.27 | BSC |
| A2 | 0.0886 | 0.1004 | 2.25 | 2.55 | E5 | 0.2854 | - | 7.25 | - |
| A3 | 0.0004 | 0.0098 | 0.01 | 0.25 | H | 0.5768 | 0.6043 | 14.65 | 15.35 |
| b | 0.0197 | 0.0276 | 0.50 | 0.70 | H2 | 0.0315 | 0.0472 | 0.80 | 1.20 |
| b1 | 0.0228 | 0.0331 | 0.58 | 0.84 | L | 0.0945 | 0.1181 | 2.40 | 3.00 |
| c | 0.0157 | 0.0236 | 0.40 | 0.60 | L1 | 0.0335 | 0.0453 | 0.85 | 1.15 |
| D | 0.3563 | 0.3720 | 9.05 | 9.45 | L4 | 0.0098 | BSC | 0.25 | BSC |
| D4 | 0.2717 | - | 6.90 | - | θ | 2° | 8° | 2° | 8° |

Notes : 1.Controlling dimension : millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material :

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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